

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (currently amended) A method for the cleaning of an integrated circuit substrate, comprising:

contacting the integrated circuit substrate with an aqueous composition comprising an effective amount a combination of (a) hydrogen fluoride, followed by (b) a mixture of hydrogen peroxide with a compound selected from the group consisting of ammonium hydroxide, hydrochloric acid and sulfuric acid, wherein ~~by products of a high-k dielectric dry etch process are removed from the integrated circuit substrate~~ said cleaning further comprises contacting the integrated circuit substrate with the combination at a temperature from about 15° C to about 90° C.

2. (currently amended) The method as recited in claim 1, wherein the aqueous composition combination comprises from about 0.05 to about 30 percent of hydrogen fluoride based on the volume of the composition combination.

3. (currently amended) The method as recited in claim 1, wherein the aqueous composition combination comprises from about 0.05 to about 30 percent of ammonium hydroxide based on the volume of the composition combination.

4. (currently amended) The method as recited in claim 1, wherein the aqueous composition combination comprises from about 0.05 to about 30 percent of hydrogen peroxide based on the volume of the composition combination.

5. (canceled)

6. (currently amended) The method as recited in claim 1, wherein said cleaning comprises contacting the integrated circuit substrate with the ~~aqueous cleaning composition combination~~ from about 10 seconds to about 10 minutes.

7. (original) The method as recited in claim 1, wherein said cleaning further comprises megasonic physical cleaning.

8-18. (canceled)